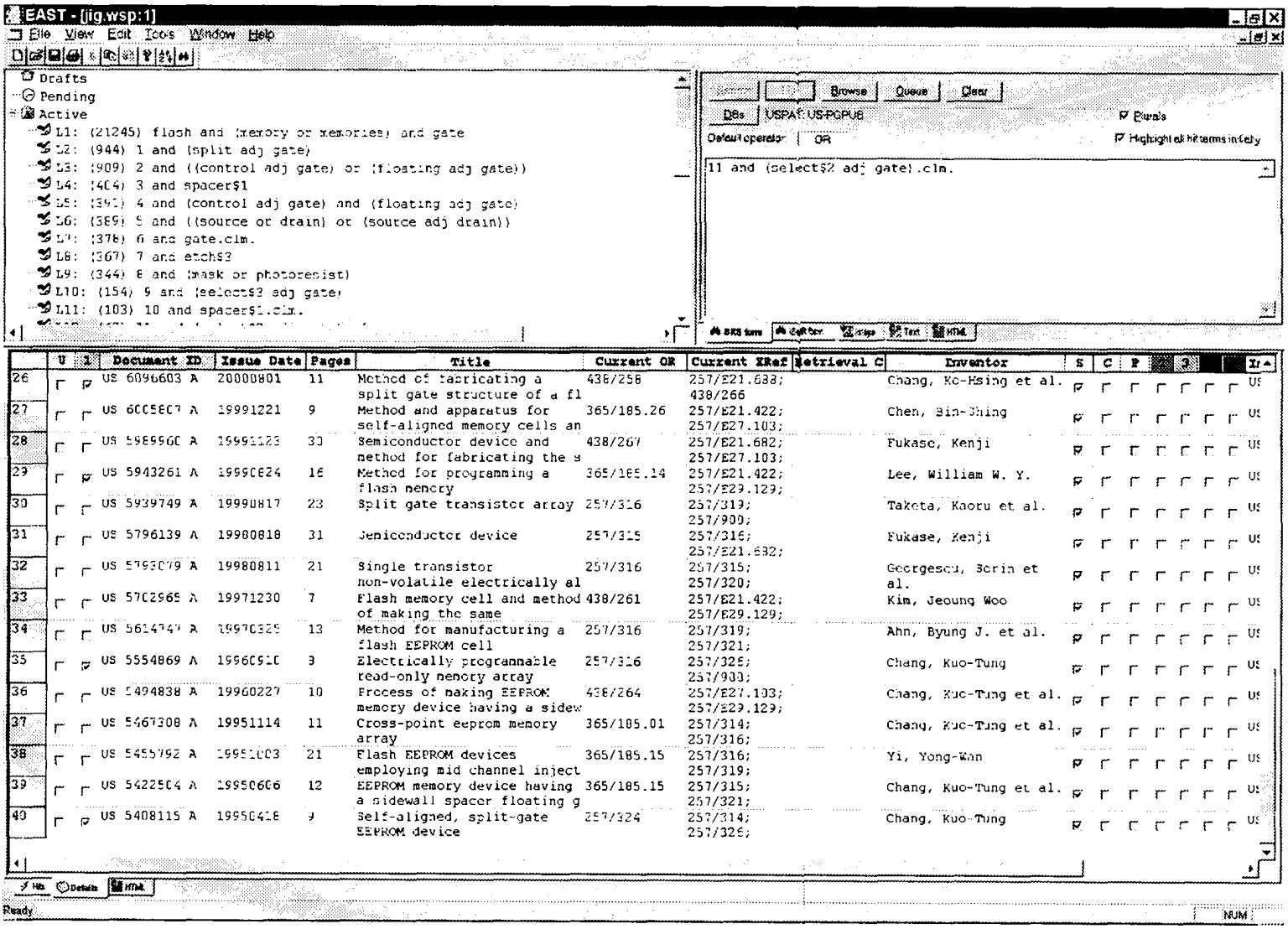

	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	Retrieval C	Inventor	S	C	P	Ir
26	☐	☑	US 6096603 A	20000801	11	Method of fabricating a split gate structure of a fl	438/258	257/E21.688; 438/266		Chang, Ko-Hsing et al.	☑	☐	☐	US
27	☐	☐	US 6005807 A	19991221	9	Method and apparatus for self-aligned memory cells an	365/185.26	257/E21.422; 257/E27.103;		Chen, Bin-Shing	☑	☐	☐	US
28	☐	☐	US 5989960 A	19991123	30	Semiconductor device and method for fabricating the s	438/267	257/E21.682; 257/E27.103;		Fukase, Kenji	☑	☐	☐	US
29	☐	☑	US 5943261 A	19990824	16	Method for programming a flash memory	365/185.14	257/E21.422; 257/E29.129;		Lee, William W. Y.	☑	☐	☐	US
30	☐	☐	US 5939749 A	19990817	23	Split gate transistor array	257/316	257/319; 257/900;		Taketa, Kaoru et al.	☑	☐	☐	US
31	☐	☐	US 5796139 A	19980818	31	Semiconductor device	257/315	257/316; 257/E21.682;		Fukase, Kenji	☑	☐	☐	US
32	☐	☐	US 5793079 A	19980811	21	Single transistor non-volatile electrically al	257/316	257/315; 257/320;		Georgescu, Sorin et al.	☑	☐	☐	US
33	☐	☐	US 5702965 A	19971230	7	Flash memory cell and method of making the same	438/261	257/E21.422; 257/E29.129;		Kim, Jeoung Woo	☑	☐	☐	US
34	☐	☐	US 5614747 A	19970325	13	Method for manufacturing a flash EEPROM cell	257/316	257/319; 257/321;		Ahn, Byung J. et al.	☑	☐	☐	US
35	☐	☑	US 5554869 A	19960910	8	Electrically programmable read-only memory array	257/316	257/325; 257/900;		Chang, Kuo-Tung	☑	☐	☐	US
36	☐	☐	US 5494838 A	19960227	10	Process of making EEPROM memory device having a sidew	438/264	257/E27.103; 257/E29.129;		Chang, Kuo-Tung et al.	☑	☐	☐	US
37	☐	☐	US 5467308 A	19951114	11	Cross-point eeprom memory array	365/185.01	257/314; 257/316;		Chang, Kuo-Tung et al.	☑	☐	☐	US
38	☐	☐	US 5455792 A	19951003	21	Flash EEPROM devices employing mid channel inject	365/185.15	257/316; 257/319;		Yi, Yong-Wan	☑	☐	☐	US
39	☐	☐	US 5422504 A	19950606	12	EEPROM memory device having a sidewall spacer floating g	365/185.15	257/315; 257/321;		Chang, Kuo-Tung et al.	☑	☐	☐	US
40	☐	☑	US 5408115 A	19950418	9	Self-aligned, split-gate EEPROM device	257/324	257/314; 257/326;		Chang, Kuo-Tung	☑	☐	☐	US